

3. (Twice Amended) A semiconductor laser device with a spot-size converter according to claim 1, wherein

another semiconductor layer is provided on a boundary plane between the semiconductor laser region and semiconductor layer, and the refractive index of the another semiconductor layer is approximately constant.

7. (Twice Amended) A semiconductor laser device with a spot-size converter according to claim 3, wherein the semiconductor laser device having a spot-size converter includes a further light waveguide region at an opposite side of the semiconductor laser region facing to the semiconductor layer.

8. (Twice Amended) A semiconductor laser device with a spot-size converter according to claim 4, wherein the semiconductor laser device having a spot-size converter includes a further light waveguide region at an opposite side of the semiconductor laser region facing to the semiconductor layer.

REMARKS

Claims 1-8 are pending.

Claim 1 is an independent claim. Claims 2-8 depend either directly on the independent claim or through intervening claims.